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SEMICONDUCTOR DEVICE



ABSTRACT OF THE DISCLOSURE

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There is provided a semiconductor device in which fabrication steps can be reduced by constructing a circuit using only TFTs of one conductivity type and in which a voltage
5 amplitude of an output signal can be normally obtained. A capacitance (205) is provided between a gate and a source of a TFT (203) connected to an output node, and a circuit formed of TFTs (201) and (202) has a function to bring a node α into a floating state. When the node α is in the floating state, a potential of the node α is caused higher than VDD by using gate-source capacitance coupling of the TFT (203) through the capacitance (205), thus an output
10 signal having an amplitude of VDD-GND can be normally obtained without causing amplitude attenuation due to the threshold value of the TFT.